

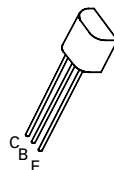
# PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

## ZTX749

ISSUE 1 – APRIL 94

### FEATURES

- \* 25 Volt  $V_{CEO}$
- \* 2 Amp continuous current
- \* Low saturation voltage



E-Line  
TO92 Compatible

### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	-35	V
Collector-Emitter Voltage	$V_{CEO}$	-25	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Peak Pulse Current	$I_{CM}$	-6	A
Continuous Collector Current	$I_C$	-2	A
Power Dissipation at $T_{amb}=25^{\circ}C$ derate above $25^{\circ}C$	$P_{tot}$	1 5.7	W mW/ $^{\circ}C$
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-35			V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-25			V	$I_C = -10mA, I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu A, I_C = 0$
Collector Cut-Off Current	$I_{CBO}$			-0.1 -10	$\mu A$ $\mu A$	$V_{CB} = -30V$ $V_{CB} = -30V, T_{amb} = 100^{\circ}C$
Emitter Cut-Off Current	$I_{EBO}$			-0.1	$\mu A$	$V_{EB} = -4V, I_E = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.12 -0.23	-0.3 -0.5	V V	$I_C = 1A, I_B = -100mA^*$ $I_C = 2A, I_B = -200mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	-1.25	V	$I_C = 1A, I_B = -100mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.8	-1	V	$I_C = -1A, V_{CE} = -2V^*$
Static Forward Current Transfer Ratio	$h_{FE}$	70 100 75 15	200 200 150 50	300		$I_C = -50mA, V_{CE} = -2V^*$ $I_C = -1A, V_{CE} = -2V^*$ $I_C = -2A, V_{CE} = -2V^*$ $I_C = -6A, V_{CE} = -2V^*$

\*Measured under pulsed conditions. Pulse width=300 $\mu s$ . Duty cycle  $\leq 2\%$

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## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

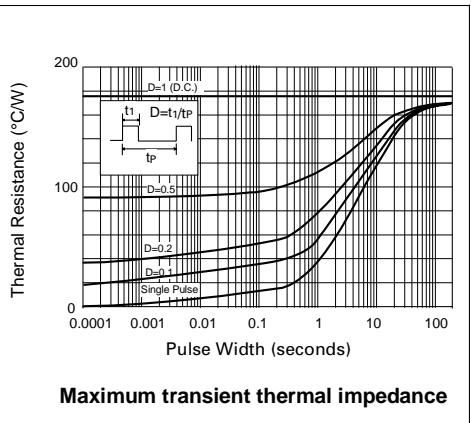
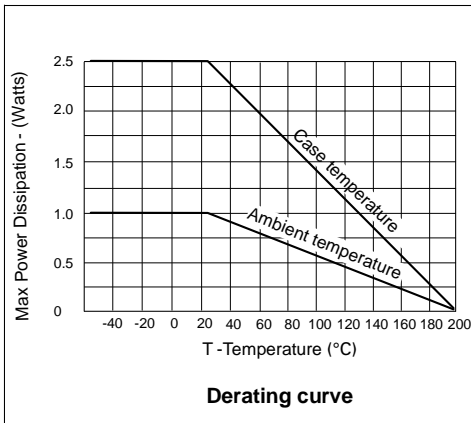
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Transition Frequency	$f_T$	100	160		MHz	$I_C = -100\text{mA}$ , $V_{CE} = -5\text{V}$ $f = 100\text{MHz}$
Output Capacitance	$C_{obo}$		55	100	pF	$V_{CB} = -10\text{V}$ $f = 1\text{MHz}$
Switching Times	$t_{on}$		40		ns	$I_C = -500\text{mA}$ , $V_{CC} = -10\text{V}$ $I_{B1} = I_{B2} = -50\text{mA}$
	$t_{off}$		450		ns	

\*Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

## THERMAL CHARACTERISTICS

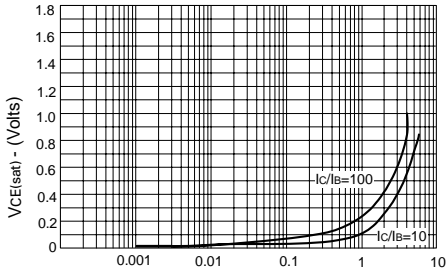
PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient <sub>1</sub>	$R_{th(j-amb)1}$	175	$^{\circ}\text{C/W}$
Junction to Ambient <sub>2</sub>	$R_{th(j-amb)2}$ †	116	$^{\circ}\text{C/W}$
Junction to Case	$R_{th(j-case)}$	70	$^{\circ}\text{C/W}$

† Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.



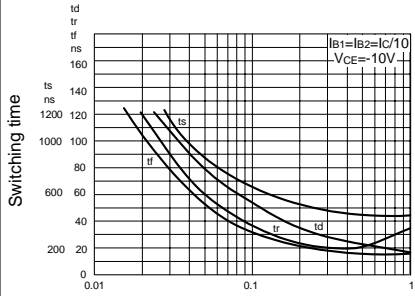
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## TYPICAL CHARACTERISTICS



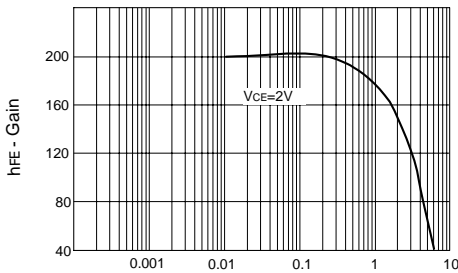
IC - Collector Current (Amps)

**VCE(sat) v IC**



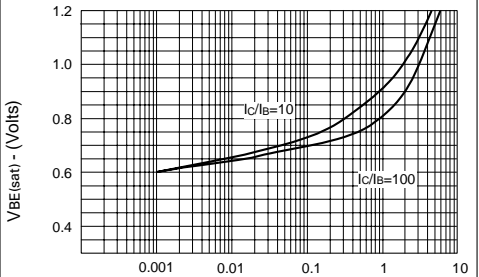
IC - Collector Current (Amps)

**Switching Speeds**



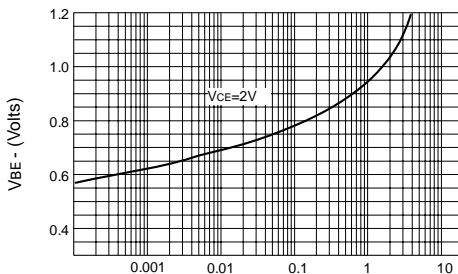
IC - Collector Current (Amps)

**hFE v IC**



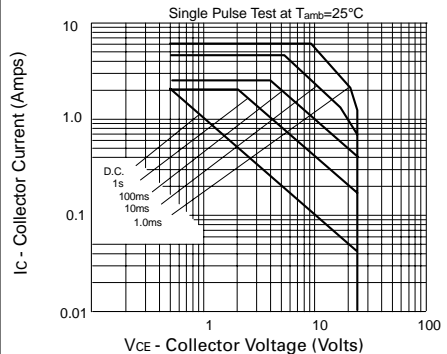
IC - Collector Current (Amps)

**VBE(sat) v IC**



IC - Collector Current (Amps)

**VBE(on) v IC**



VCE - Collector Voltage (Volts)

**Safe Operating Area**